2SC5632G

Silicon NPN epitaxial planar type

For high-frequency amplification and switching

Features

- High transition frequency f_T
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

SMini3-F2 Marking Symbol: 28

Package Code

Absolute Maximum Ratings $T_a = 25^{\circ}C$

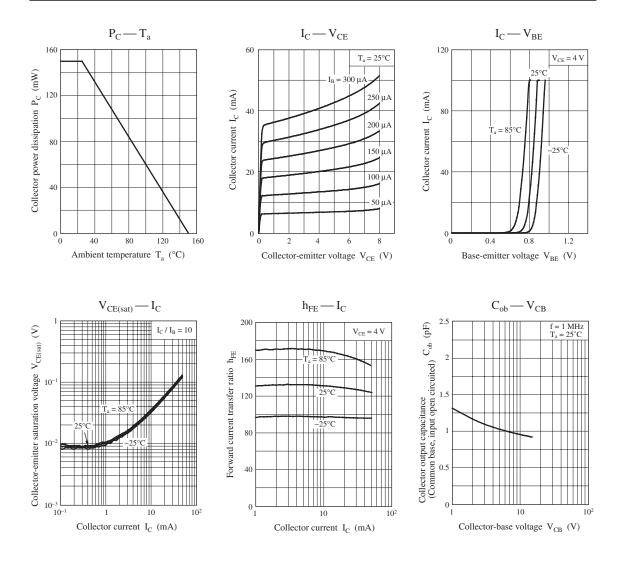
 S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing Absolute Maximum Ratings T_a = 25°C 					SMini3- Marking Pin Nar Base E Emitt Colle	y Symb ne	iol; 28	'n6.		
Parameter	Symbol	Rating	Unit		<i>²<i>Q</i></i>	10				
Collector-base voltage (Emitter open)	V _{CBO}	15	V	ر پر C	У°_6	, o		<u>G</u> .		
Collector-emitter voltage (Base open)	V _{CEO}	8	V	0	NS.	-	. در 9	5		
Emitter-base voltage (Collector open)	V _{EBO}	3	G.V.	<u>ଡ</u> ି (<i>,</i> 0	0	SU.			
Collector current	I _C	50	mA	Je le		S				
Collector power dissipation	P _C	150	COW V	Q.	-					
Junction temperature	Tj	V150 Q	°C		<u>ر</u> ح					
Storage temperature	T _{stg}	255 to +150	39		\mathcal{Y}					
■ Electrical Characteristics T, 25°C, 43°C, Contact										
Parameter	Symbo		Conditio	ons		Min	Тур	Мах		
Collector-base voltage (Emitter open)	Сво	$H_{\rm C} = 100 \mu$	A, $I_{E} = 0$			15				
Emitter-base cutoff current (Collector open)		$V_{EB} = 2 V$, I _C = 0					2		
Forward current transfer ratio	h _{FE}	$O_{CE} = 4 V$	$, I_{\rm C} = 2 {\rm mA}$			100		350		

Electrical Characteristics

	$C \sim$					
Parameter 0	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitte Open)	Сво	$F_{\rm C} = 10004$ A, $I_{\rm E} = 0$	15			V
Emitter-base cutoff current (Collector open)	IEBO	$V_{EB} = 2 V, I_C = 0$			2	μΑ
Forward current transfer ratio	h _{FE}	$V_{CE} = 4 \text{ V}, \text{ I}_{C} = 2 \text{ mA}$	100		350	_
h _{FE} ratio	Δh_{FE}	h_{FE2} : $V_{CE} = 4 V$, $I_C = 100 \mu A$	0.6		1.5	_
alt of all of	\mathcal{L}	h_{FE1} : $V_{CE} = 4 V$, $I_C = 2 mA$				
Coffector-emitter saturation voltage	V _{CE(sat)}	$I_{C} = 20 \text{ mA}, I_{B} = 4 \text{ mA}$			0.1	V
Transition frequency	f _T	$V_{CE} = 5 \text{ V}, I_C = 15 \text{ mA}, f = 200 \text{ MHz}$	0.6	1.1		GHz
Collector output capacitance	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		1.0	1.6	pF
(Common base, mput open circuited)						

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: $\Delta h_{FE} \neq h_{FE2} / h_{FE1}$

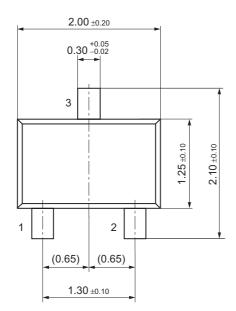
Panasonic

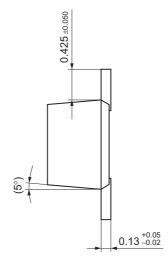


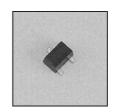
Panasonic

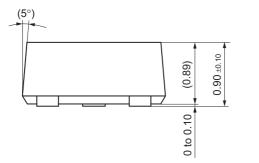
SMini3-F2

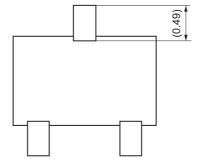
Unit: mm











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